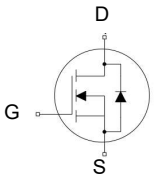
30V N-Channel Power SpeedFET

● General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Product Summary



V_{DS}= 30V

$R_{DS(ON)}$ = 1mΩ

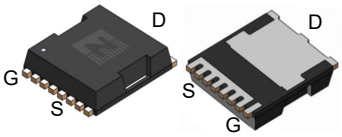
I_D= 230A

● Features

■Low $R_{DS(ON)}$ to minimize conductive loss

■Low Gate Charge for fast switching

■Low Thermal resistance



RoHS

●Application

■BLDC Motor driver

■DC-DC

■Battery protection

TOLL

REACH COMPLIANT

HF

●Ordering Information:

Part NO.	ZMS006N03R
Marking	ZMS006N03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2000

●Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		30	V
Gate-Source Voltage	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25℃	230	A
	I_D	T_C=75℃	166	A
	I_D	T_C=100℃	139	A
Pulsed Drain Current	I_{DM}	Pulsed; t_p ≤ 10 μs; T_{mb} = 25 °C;	690	A
Total Power Dissipation	P_D	T_C=25℃	250	W
Total Power Dissipation	P_D	T_A=25℃	4.2	W
Operating Junction Temperature	T_J		-55 to +150	℃
Storage Temperature	T_{STG}		-55 to +150	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=10V, Rg=25Ω,	450	mJ
		L=0.5mH, V_{GS}=10V, Rg=25Ω,	1035	mJ
ESD Level (HBM)	CLASS 2			

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.5	°C/W
Thermal resistance, junction-ambient	R_{thJA} ①		-	30	°C/W
Soldering temperature	Tsold		-	260	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250uA	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	1.2	1.8	2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= 30V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} = 0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D= 70A		1.6	2.1	mΩ
		V_{GS}=10V, I_D= 100A		1	1.3	
Forward Transconductance	g_{FS}	V_{DS} =5V, I_{SD} = 100A		32		s
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = 100A			1.3	V

●Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=25V	-	6558	-	pF
Output capacitance	Coss		-	1354	-	
Reverse transfer capacitance	Crss		-	121	-	
Gate Risistance	Rg	f = 1MHz	-	2.2		Ω
Total gate charge	Qg	V_{DD} = 15V, I_D = 100A, V_{GS} = 10V	-	114	-	nC
Gate - Source charge	Qgs		-	11	-	
Gate - Drain charge	Qgd		-	33	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=15V, R_G =3.3Ω, I_D =20A	-	26	-	ns
Turn-ON Rise time	t_r		-	27	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	68	-	ns
Turn-Off Fall time	t_f		-	16	-	ns
Reverse Recovery Time	t_{RR}	V_{DD}=20V, dI_S/dt = 100A/us, I_S=50A	-	68	-	ns
Reverse Recovery Charge	Q_{RR}		-	98	-	nC

Fig.1 Gate-Charge Characteristics

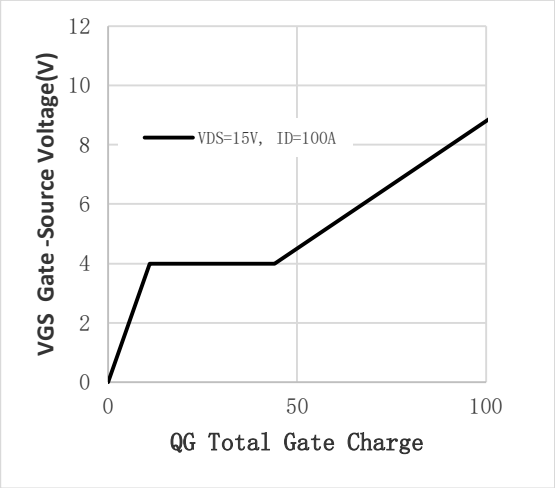


Fig.2 Capacitance Characteristics

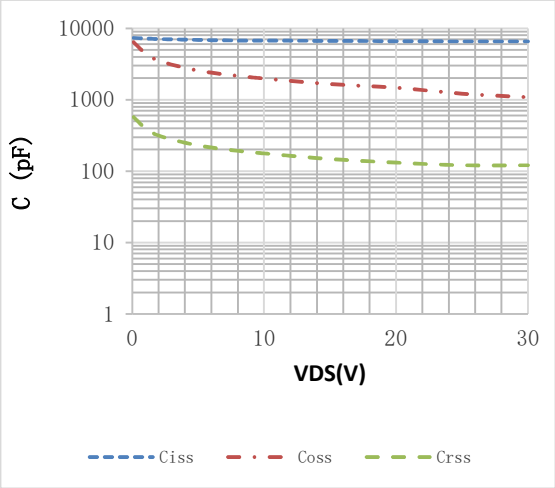


Fig.3 Power Dissipation

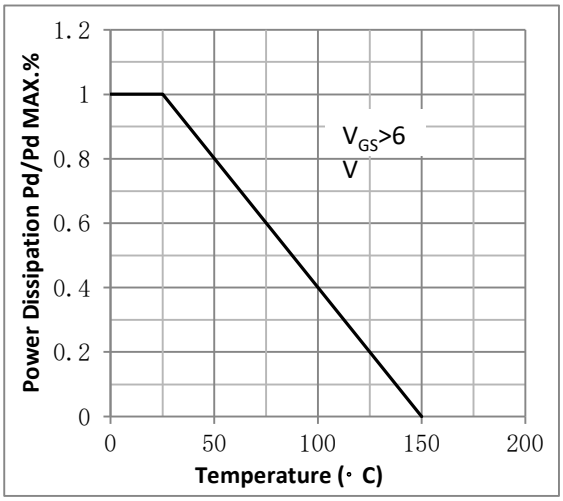


Fig.4 Typical output Characteristics

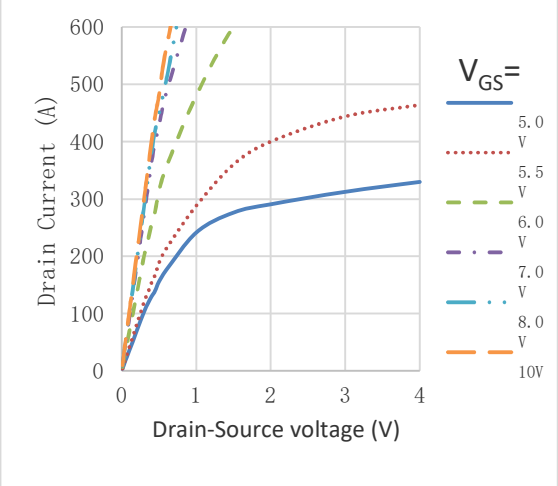


Fig.5 Threshold Voltage V.S Junction Temperature

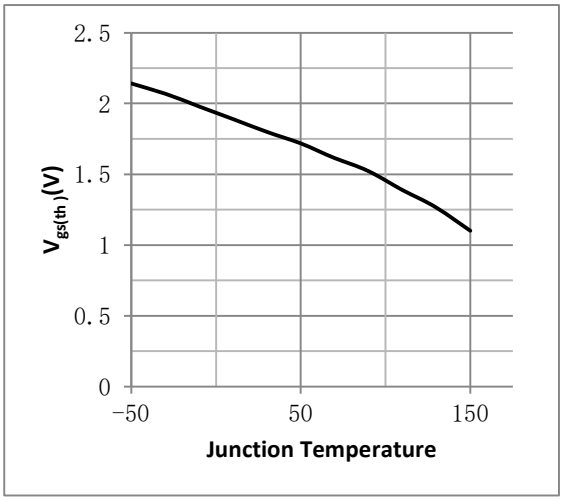


Fig.6 Resistance V.S Drain Current

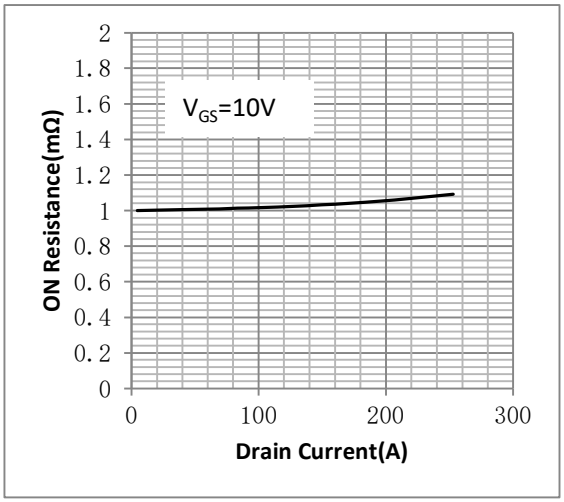


Fig.7 On-Resistance VS Gate Source Voltage

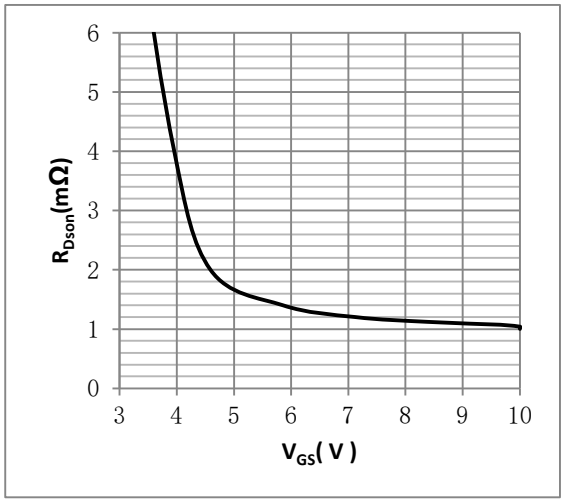


Fig.8 On-Resistance V.S Junction Temperature

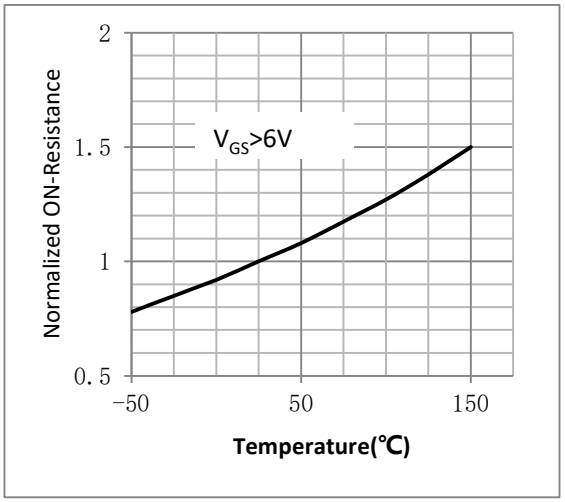


Figure 9. Diode Forward Voltage vs. Current

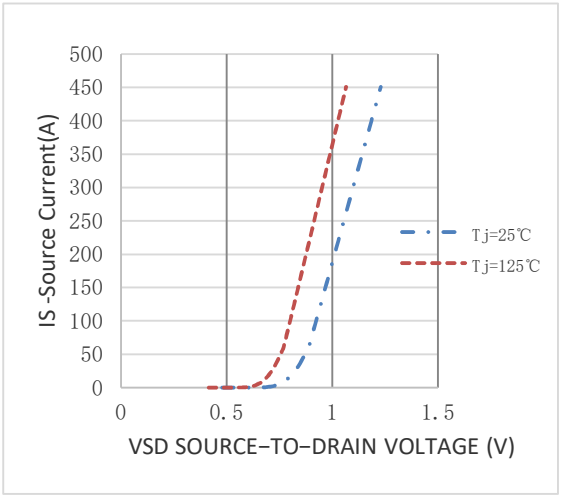


Figure 10. Transfer Characteristics

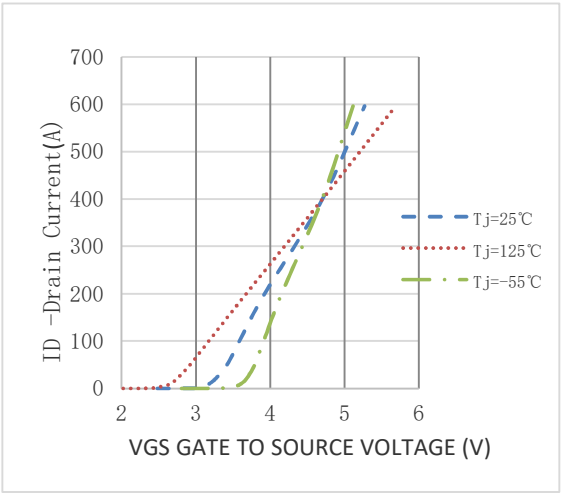


Fig.11 Safe Operating Area

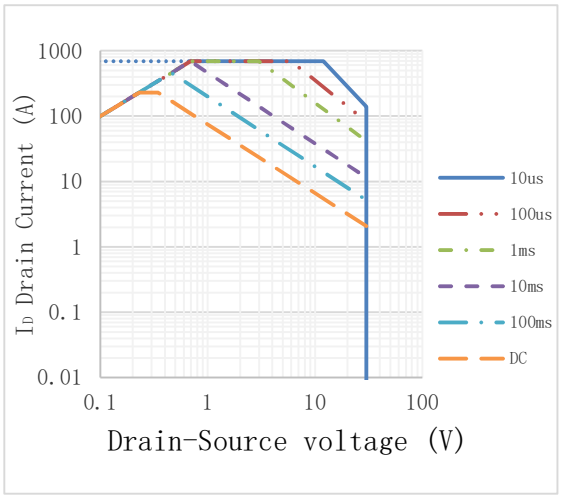
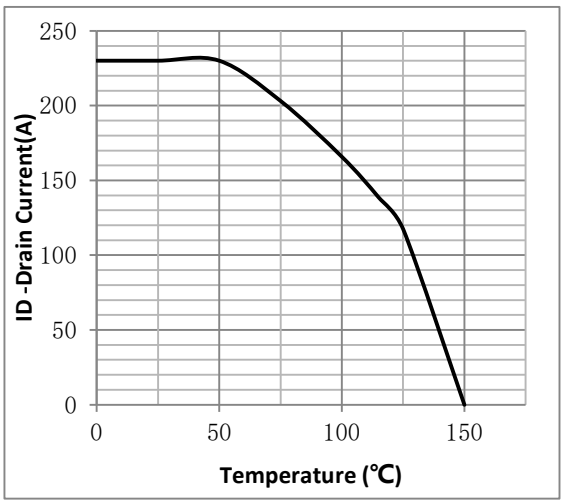
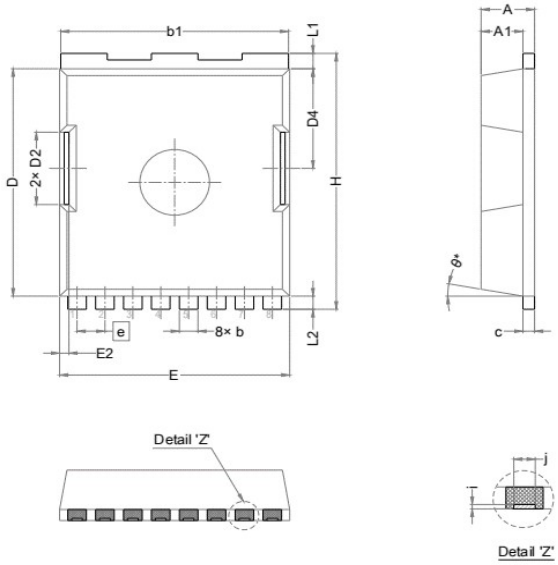
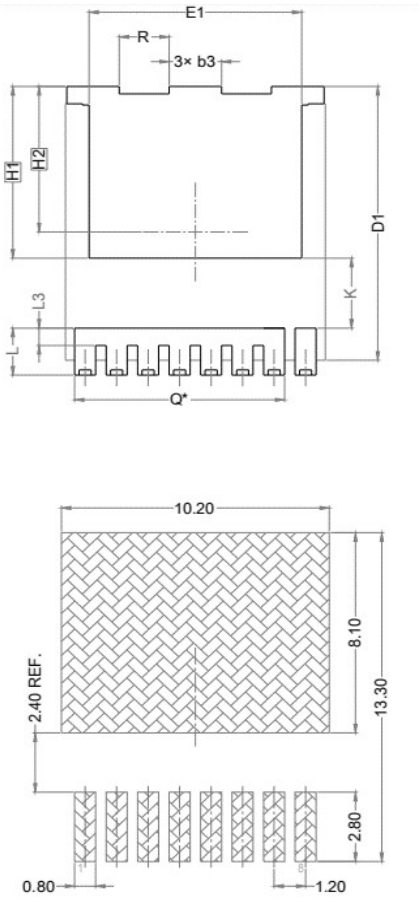


Fig.12 ID vs. Junction Temperature②



●TOLL Package Outline





SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b3	1.90	2.00	2.10
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D4	4.45	4.55	4.65
E	9.80	9.90	10.00
E1	8.00	8.10	8.20
E2	0.30	0.40	0.50
e	1.20 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
H2	5.89 BSC		
i	0.10 REF.		
j	0.46 REF.		
K	2.80 REF.		
L	1.60	1.90	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.60	0.70	0.80
N	8		
Q	6.80 REF.		
R	1.80	1.90	2.00
θ	10° REF.		

Note:

①Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

②Practically the current will be limited by PCB, thermal design and operating temperature. V_{GS}=10V.

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Revision History

Version	Date	Change
A	2022.1.6	NEW
B	2024.5.6	Correct ID 、 IDM and dynamic curves.
C	2024.5.21	Correct BVDSS, RDSON Vgs voltage, Qg current